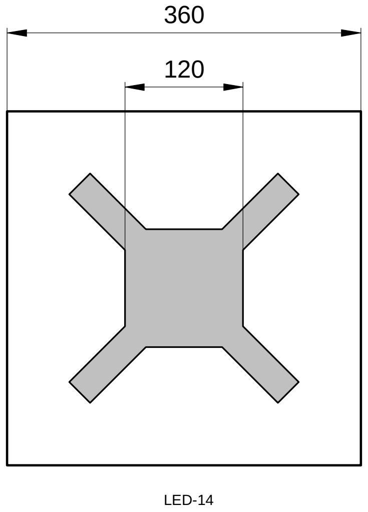
LED - Chip ELC-880-17

01.07.2011 rev. 10

Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	P (anode) up



typ. dimensions (µm)

typ. thickness

160 (±20) µm

anode

gold alloy, 1.5 µm

cathode

gold alloy, 0.5 µm,
structured, 25% covered

Optical and Electrical Characteristics

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.35	1.6	V
Reverse voltage	I_R = 100 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e	3.5	5.0		mW
Radiant power[2]	I_F = 20 mA	Φ_e		10.0		mW
Peak wavelength	I_F = 20 mA	λ_p	860	875	890	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		45		nm
Switching time	I_F = 20 mA	t_r, t_f		10/20		ns

[1] Measured on bare chip on TO-18 header with JENOPTIK Polymer Systems equipment

[2] Measured on epoxy covered chip on TO-18 header with JENOPTIK Polymer Systems equipment

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	Quantity
ELC-880-17				

Packing: Chips on adhesive film with wire-bond side on top